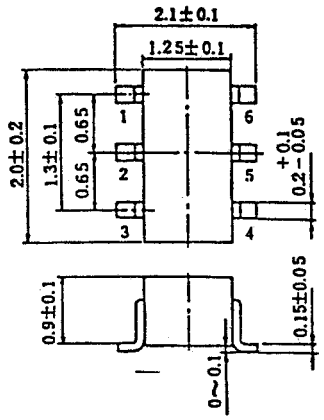
TOSHIBA Diode Silicon Epitaxial Planar Type

HN2D01FU

Ultra High Speed Switching Application

- HN2D01FU is composed of 3 independent diodes.
- Low forward voltage : $V_{F\ (3)}$ = 0.98V (typ.)
- Fast reverse recovery time : t_{rr} = 1.6ns (typ.)
- Small total capacitance : C_T = 0.5pF (typ.)

Unit in mm



1. CATHODE
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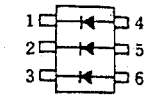
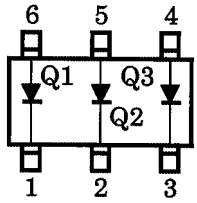


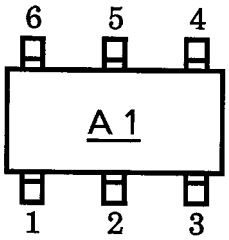
JEDEC	—
EIAJ	—
TOSHIBA	1-2T1C

Weight: 6.2mg

Pin Assignment (Top View)



Marking



Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse Voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Maximum (peak) forward current	I_{FM}	240 *	mA
Average forward current	I_O	80 *	mA
Surge current (10ms)	I_{FSM}	1 *	A
Power dissipation	P	200	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	−55~125	°C

* : This is maximum rating of single diode (Q1 or Q2 or Q3). In the case of using 2 ro 3 diodes, the maximum ratings per diodes is 75 % of the single diode one.

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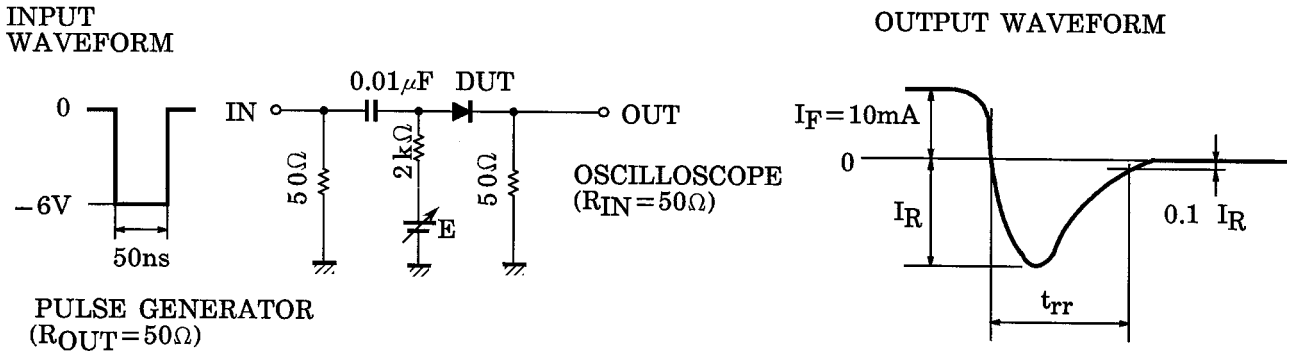
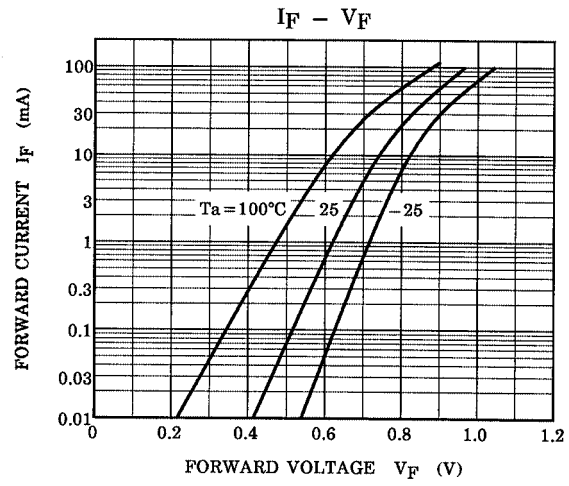
Electrical Characteristics (Q1 Q2 Q3 Common, Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_{F\ (1)}$	—	I_F = 1mA	—	0.62	—	V
	$V_{F\ (2)}$	—	I_F = 10mA	—	0.75	—	
	$V_{F\ (3)}$	—	I_F = 100mA	—	0.98	1.20	
Reverse current	$I_{R\ (1)}$	—	V_R = 30V	—	—	0.1	μA
	$I_{R\ (2)}$	—	V_R = 80V	—	—	0.5	
Total capacitance	C_T	—	V_R = 0, f = 1MHz	—	0.5	3.0	pF
Reverse recovery time	t_{rr}	—	I_F = 10mA (Fig.1)	—	1.6	4.0	ns

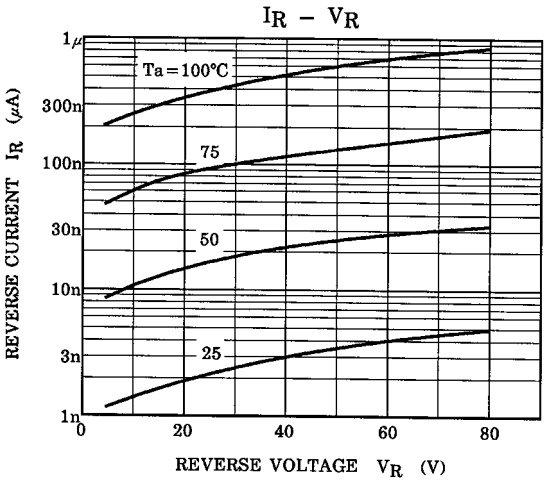
Fig.1 Reverse Recovery Time (t_{rr}) Test Circuit



Q1, Q2, Q3 Common



Q1, Q2, Q3 Common



Q1, Q2, Q3 Common